

Hiroyuki Sazawa

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/9223178/publications.pdf>

Version: 2024-02-01

18
papers

330
citations

1307594

7
h-index

940533

16
g-index

18
all docs

18
docs citations

18
times ranked

291
citing authors

#	ARTICLE	IF	CITATIONS
1	Ion-channel sensors. <i>Analytical Chemistry</i> , 1987, 59, 2842-2846.	6.5	193
2	Nitride passivation reduces interfacial traps in atomic-layer-deposited Al ₂ O ₃ /GaAs (001) metal-oxide-semiconductor capacitors using atmospheric metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2014, 105, .	3.3	31
3	Effect of the membrane surface charge on the host-guest complex of valinomycin in a synthetic lipid monolayer at the air-water interface. <i>Langmuir</i> , 1992, 8, 609-612.	3.5	26
4	Reduction in Buffer Leakage Current with Mn-Doped GaN Buffer Layer Grown by Metal Organic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JN12.	1.5	15
5	Electrical properties of GaAs metal-oxide-semiconductor structure comprising Al ₂ O ₃ gate oxide and AlN passivation layer fabricated in situ using a metal-organic vapor deposition/atomic layer deposition hybrid system. <i>AIP Advances</i> , 2015, 5, 087149.	1.3	15
6	High-mobility 2D electron gas in carbon-face 3C-SiC/4H-SiC heterostructure with single-domain 3C-SiC layer. <i>Applied Physics Letters</i> , 2022, 120, .	3.3	12
7	Spontaneous polarization and band gap bowing in Y _x Al _y Ga _{1-x-y} N alloys lattice-matched to GaN. <i>Journal of Applied Physics</i> , 2011, 110, 074114.	2.5	9
8	Factors Affecting Background Permeabilities of Ordered Mono-, Bi- and Multilayers as Channel Mimetic Sensing Membranes. <i>Analytical Sciences</i> , 1994, 10, 343-347.	1.6	7
9	A low-leakage and reduced current collapse AlGa _x /GaN heterojunction field effect transistor with AlO _x gate insulator formed by metal-organic chemical vapor deposition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 1986-1988.	0.8	4
10	First-principles study of spontaneous polarization and band gap bowing in Sc _x Al _y Ga _{1-x-y} N alloys lattice-matched to GaN. <i>Semiconductor Science and Technology</i> , 2012, 27, 105014.	2.0	4
11	High-performance GaAs-based metal-oxide-semiconductor heterostructure field-effect transistors with atomic-layer-deposited Al ₂ O ₃ gate oxide and in situ AlN passivation by metalorganic chemical vapor deposition. <i>Applied Physics Express</i> , 2014, 7, 106502.	2.4	4
12	Correlation between micropipes on SiC substrate and dc characteristics of AlGa _{1-x} GaN high-electron mobility transistors. <i>Journal of Applied Physics</i> , 2006, 100, 114502.	2.5	3
13	Influence of macro defects in SiC substrate on AlGa _x /GaN HEMT DC characteristics. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 2321-2324.	0.8	2
14	rf-MBE growth and characterizations of AlGa _x /GaN HEMTs on vicinal sapphire (0001) substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 1995-1997.	0.8	2
15	Influence of Micropipe and Domain Boundary in SiC Substrate on the DC Characteristics of AlGa _x /GaN HFET. <i>Materials Science Forum</i> , 2007, 556-557, 1043-1046.	0.3	1
16	Improved Contact Resistance in AlGa _x /GaN Heterostructures by Titanium Distribution Control at the Metal-Semiconductor Interface. <i>Applied Physics Express</i> , 0, 1, 081101.	2.4	1
17	Electronic Structure and Spontaneous Polarization in Sc _x Al _y Ga _{1-x-y} N Alloys Lattice-Matched to GaN: A First-Principles Study. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JM04.	1.5	1
18	A study on influence of micropipes in SiC substrate on overgrown AlGa _x /GaN HEMT DC characteristics. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 1662-1666.	0.8	0